

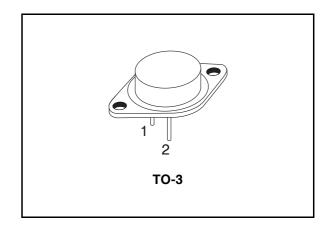
## High power NPN silicon transistor

### **General features**

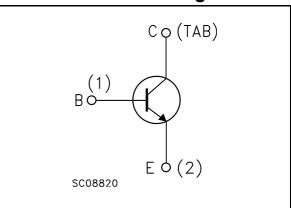
■ STMicroelectronics preferred salestype

### **Description**

The device is a silicon planar NPN transistor mounted in Jedec TO-3 metal case. It is intended for linear amplifiers and inductive switching applications.



## Internal schematic diagram



### **Order codes**

| Part Number | Marking | Package | Packing |
|-------------|---------|---------|---------|
| 2N3773      | 2N3773  | TO-3    | Bag     |

Electrical ratings 2N3773

# 1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol           | Parameter   | Value      | Unit |
|------------------|---|------------|------|
| V <sub>CEO</sub> | Collector-emitter voltage (I <sub>B</sub> = 0)      | 140        | V    |
| V <sub>CEV</sub> | Collector-emitter voltage (V <sub>BE</sub> = -1.5V) | 160        | V    |
| V <sub>CBO</sub> | Collector-base voltage (I <sub>E</sub> = 0)         | 160        | V    |
| V <sub>EBO</sub> | Emitter-base voltage ( $I_C = 0$ )                  | 7          | V    |
| I <sub>C</sub>   | Collector current                                   | 16         | Α    |
| I <sub>CM</sub>  | Collector peak current (t <sub>P</sub> < 5ms)       | 30         | Α    |
| I <sub>B</sub>   | Base current  |            | Α    |
| I <sub>BM</sub>  | Base peak current (t <sub>P</sub> < 1ms)            |            | Α    |
| P <sub>tot</sub> | Total dissipation at T <sub>c</sub> ≤ 25°C          |            | W    |
| T <sub>stg</sub> | Storage temperature                                 | -65 to 200 | °C   |

Table 2. Thermal data

| Symbol                | Parameter                        | Value | Unit |      |
|-----------------------|----------------------------------|-------|------|------|
| R <sub>thj-case</sub> | Thermal resistance junction-case | Max   | 1.17 | °C/W |

## 2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$ 

Table 3. Electrical characteristics

| Symbol                         | Parameter  | Test Conditions                                  |  | Min.    | Тур. | Max.     | Unit     |
|--------------------------------|--|--|--|---------|------|----------|----------|
| I <sub>CEV</sub>               | Collector cut-off current (V <sub>BE</sub> = -1.5V)            | V <sub>CB</sub> = 140V<br>V <sub>CB</sub> = 140V | T <sub>j</sub> = 150°C                       |         |      | 2<br>10  | mA<br>mA |
| I <sub>CEO</sub>               | Collector cut-off current (I <sub>B</sub> = 0)                 | V <sub>CB</sub> = 120V                           |  |         |      | 10       | mA       |
| I <sub>CBO</sub>               | Collector cut-off current (I <sub>E</sub> = 0)                 | V <sub>CB</sub> = 140V                           |  |         |      | 2        | mA       |
| I <sub>EBO</sub>               | Emitter cut-off current (I <sub>C</sub> = 0)                   | V <sub>CB</sub> = 7V                             |  |         |      | 5        | mA       |
| V <sub>CEO(sus)</sub> (1)      | Collector-emitter sustaining voltage (I <sub>B</sub> = 0)      | I <sub>C</sub> = 0.2A                            |  | 140     |      |          | V        |
| V <sub>CEV(sus)</sub> (1)      | Collector-emitter sustaining voltage (V <sub>EB</sub> = -1.5V) | I <sub>C</sub> = 0.2A                            |  | 160     |      |          | V        |
| V <sub>CER(sus)</sub> (1)      | Collector-emitter sustaining voltage (R <sub>BE</sub> = 100Ω)  | I <sub>C</sub> = 0.2A                            |  | 150     |      |          | V        |
| V <sub>CE(sat)</sub> (1)       | Collector-emitter saturation voltage                           | I <sub>C</sub> = 8A<br>I <sub>C</sub> = 16A      | _  |         |      | 1.4<br>4 | V<br>V   |
| V <sub>BE</sub> <sup>(1)</sup> | Base-emitter voltage   | I <sub>C</sub> = 8A                              | V <sub>CE</sub> = 4V                         |         |      | 2.2      | V        |
| h <sub>FE</sub> <sup>(1)</sup> | DC current gain  | I <sub>C</sub> = 8A<br>I <sub>C</sub> = 16A      | V <sub>CE</sub> = 4V<br>V <sub>CE</sub> = 4V | 15<br>5 |      | 60       |          |
| I <sub>s/b</sub>               | Second Breakdown<br>Collector Current                          | V <sub>CE</sub> = 30V<br>t = 1s (non rep         | petitive)                                    | 5       |      |          | А        |

<sup>1.</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle  $\leq$  2 %

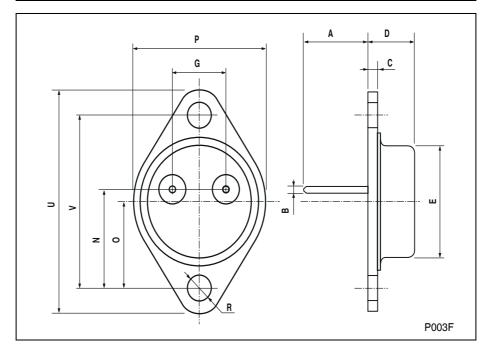
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## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

#### **TO-3 MECHANICAL DATA**

| DIM. | mm    |      |       | inch  |      |       |  |
|------|-------|------|-------|-------|------|-------|--|
| Diw. | MIN.  | TYP. | MAX.  | MIN.  | TYP. | MAX.  |  |
| Α    | 11.00 |      | 13.10 | 0.433 |      | 0.516 |  |
| В    | 0.97  |      | 1.15  | 0.038 |      | 0.045 |  |
| С    | 1.50  |      | 1.65  | 0.059 |      | 0.065 |  |
| D    | 8.32  |      | 8.92  | 0.327 |      | 0.351 |  |
| E    | 19.00 |      | 20.00 | 0.748 |      | 0.787 |  |
| G    | 10.70 |      | 11.10 | 0.421 |      | 0.437 |  |
| N    | 16.50 |      | 17.20 | 0.649 |      | 0.677 |  |
| Р    | 25.00 |      | 26.00 | 0.984 |      | 1.023 |  |
| R    | 4.00  |      | 4.09  | 0.157 |      | 0.161 |  |
| U    | 38.50 |      | 39.30 | 1.515 |      | 1.547 |  |
| V    | 30.00 |      | 30.30 | 1.187 |      | 1.193 |  |



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Revision history 2N3773

# 4 Revision history

Table 4. Revision history

| Date        | Revision | Changes          |
|-------------|----------|------------------|
| 03-Apr-2006 | 1        | Initial release. |

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